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H-1032

O.L.

4/20/02

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

T. HASHIMOTO et al

Serial No.

Filed: March 4, 2002

For: A SEMICONDUCTOR DEVICE AND A METHOD OF
MANUFACTURING THE SAME

PRELIMINARY AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

Sir:

Prior to the examination thereof, please amend the above-
identified application as follows.

IN THE CLAIMS

/ Please rewrite claim 14 as set forth below.

14. (Amended) The semiconductor device according to
claim 11, wherein the epitaxial layer is comprised mainly of
silicon-germanium, silicon-germanium-carbon, or silicon.